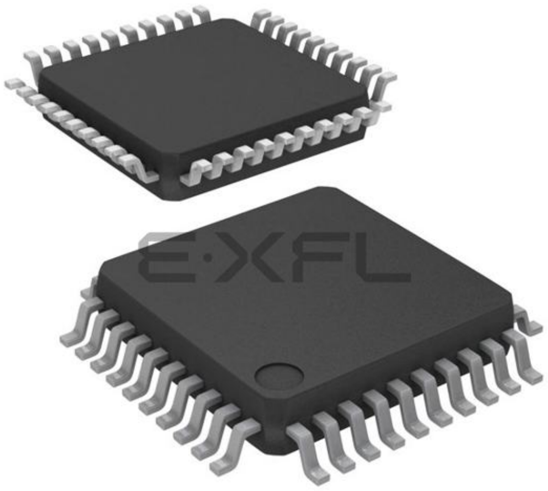
Renesas Electronics America Inc - R5F21275SDFP#V2 Datasheet



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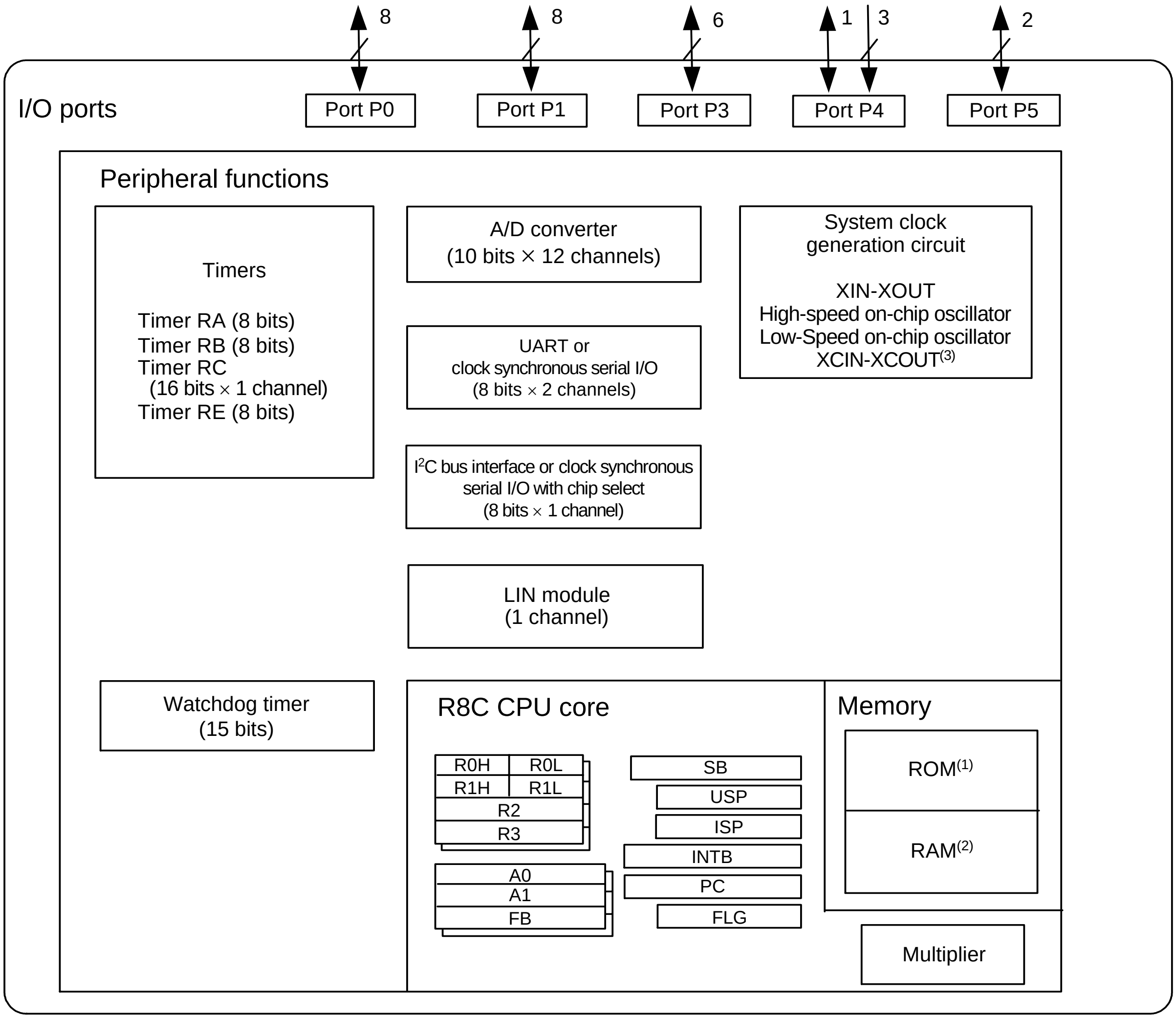
Applications of "Embedded - Microcontrollers"

Details	
Product Status	Active
Core Processor	R8C
Core Size	16-Bit
Speed	20MHz
Connectivity	I²C, LINbus, SIO, SSU, UART/USART
Peripherals	LED, POR, Voltage Detect, WDT
Number of I/O	25
Program Memory Size	24KB (24K x 8)
Program Memory Type	FLASH
EEPROM Size	2K x 8
RAM Size	1.5K x 8
Voltage - Supply (Vcc/Vdd)	2.2V ~ 5.5V
Data Converters	A/D 12x10b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 85°C (TA)
Mounting Type	Surface Mount
Package / Case	32-LQFP
Supplier Device Package	32-LQFP (7x7)
Purchase URL	https://www.e-xfl.com/product-detail/renesas-electronics-america/r5f21275sdfp-v2

1.3 Block Diagram

Figure 1.1 shows a Block Diagram.



NOTES:
1. ROM size varies with MCU type.
2. RAM size varies with MCU type.
3. XCIN, XCOUT can be used only for N or D version.

Figure 1.1 Block Diagram

1.4 Product Information

Table 1.3 lists the Product Information for R8C/26 Group and Table 1.4 lists the Product Information for R8C/27 Group.

Table 1.3 Product Information for R8C/26 Group **Current of Sep. 2008**

Part No.	ROM Capacity	RAM Capacity	Package Type	Remarks	
R5F21262SNFP	8 Kbytes	512 bytes	PLQP0032GB-A	N version	
R5F21264SNFP	16 Kbytes	1 Kbyte	PLQP0032GB-A		
R5F21265SNFP	24 Kbytes	1.5 Kbytes	PLQP0032GB-A		
R5F21266SNFP	32 Kbytes	1.5 Kbytes	PLQP0032GB-A		
R5F21262SDFP	8 Kbytes	512 bytes	PLQP0032GB-A	D version	
R5F21264SDFP	16 Kbytes	1 Kbyte	PLQP0032GB-A		
R5F21265SDFP	24 Kbytes	1.5 Kbytes	PLQP0032GB-A		
R5F21266SDFP	32 Kbytes	1.5 Kbytes	PLQP0032GB-A		
R5F21264JFP	16 Kbytes	1 Kbyte	PLQP0032GB-A	J version	
R5F21266JFP	32 Kbytes	1.5 Kbytes	PLQP0032GB-A		
R5F21264KFP	16 Kbytes	1 Kbyte	PLQP0032GB-A	K version	
R5F21266KFP	32 Kbytes	1.5 Kbytes	PLQP0032GB-A		
R5F21262SNXXXFP	8 Kbytes	512 bytes	PLQP0032GB-A	N version	Factory programming product[1]
R5F21264SNXXXFP	16 Kbytes	1 Kbyte	PLQP0032GB-A		
R5F21265SNXXXFP	24 Kbytes	1.5 Kbytes	PLQP0032GB-A		
R5F21266SNXXXFP	32 Kbytes	1.5 Kbytes	PLQP0032GB-A		
R5F21262SDXXXFP	8 Kbytes	512 bytes	PLQP0032GB-A	D version	
R5F21264SDXXXFP	16 Kbytes	1 Kbyte	PLQP0032GB-A		
R5F21265SDXXXFP	24 Kbytes	1.5 Kbytes	PLQP0032GB-A		
R5F21266SDXXXFP	32 Kbytes	1.5 Kbytes	PLQP0032GB-A		
R5F21264JXXXFP	16 Kbytes	1 Kbyte	PLQP0032GB-A	J version	
R5F21266JXXXFP	32 Kbytes	1.5 Kbytes	PLQP0032GB-A		
R5F21264KXXXFP	16 Kbytes	1 Kbyte	PLQP0032GB-A	K version	
R5F21266KXXXFP	32 Kbytes	1.5 Kbytes	PLQP0032GB-A		

NOTE:

1. The user ROM is programmed before shipment.

Table 1.4 Product Information for R8C/27 Group **Current of Sep. 2008**

Part No.	ROM Capacity		RAM Capacity	Package Type	Remarks	
	Program ROM	Data flash				
R5F21272SNFP	8 Kbytes	1 Kbyte × 2	512 bytes	PLQP0032GB-A	N version	
R5F21274SNFP	16 Kbytes	1 Kbyte × 2	1 Kbyte	PLQP0032GB-A		
R5F21275SNFP	24 Kbytes	1 Kbyte × 2	1.5 Kbytes	PLQP0032GB-A		
R5F21276SNFP	32 Kbytes	1 Kbyte × 2	1.5 Kbytes	PLQP0032GB-A		
R5F21272SDFP	8 Kbytes	1 Kbyte × 2	512 bytes	PLQP0032GB-A	D version	
R5F21274SDFP	16 Kbytes	1 Kbyte × 2	1 Kbyte	PLQP0032GB-A		
R5F21275SDFP	24 Kbytes	1 Kbyte × 2	1.5 Kbytes	PLQP0032GB-A		
R5F21276SDFP	32 Kbytes	1 Kbyte × 2	1.5 Kbytes	PLQP0032GB-A		
R5F21274JFP	16 Kbytes	1 Kbyte × 2	1 Kbyte	PLQP0032GB-A	J version	
R5F21276JFP	32 Kbytes	1 Kbyte × 2	1.5 Kbytes	PLQP0032GB-A		
R5F21274KFP	16 Kbytes	1 Kbyte × 2	1 Kbyte	PLQP0032GB-A	K version	
R5F21276KFP	32 Kbytes	1 Kbyte × 2	1.5 Kbytes	PLQP0032GB-A		
R5F21272SNXXXFP	8 Kbytes	1 Kbyte × 2	512 bytes	PLQP0032GB-A	N version	Factory programming product(1)
R5F21274SNXXXFP	16 Kbytes	1 Kbyte × 2	1 Kbyte	PLQP0032GB-A		
R5F21275SNXXXFP	24 Kbytes	1 Kbyte × 2	1.5 Kbytes	PLQP0032GB-A		
R5F21276SNXXXFP	32 Kbytes	1 Kbyte × 2	1.5 Kbytes	PLQP0032GB-A		
R5F21272SDXXXFP	8 Kbytes	1 Kbyte × 2	512 bytes	PLQP0032GB-A	D version	
R5F21274SDXXXFP	16 Kbytes	1 Kbyte × 2	1 Kbyte	PLQP0032GB-A		
R5F21275SDXXXFP	24 Kbytes	1 Kbyte × 2	1.5 Kbytes	PLQP0032GB-A		
R5F21276SDXXXFP	32 Kbytes	1 Kbyte × 2	1.5 Kbytes	PLQP0032GB-A		
R5F21274JXXXFP	16 Kbytes	1 Kbyte × 2	1 Kbyte	PLQP0032GB-A	J version	
R5F21276JXXXFP	32 Kbytes	1 Kbyte × 2	1.5 Kbytes	PLQP0032GB-A		
R5F21274KXXXFP	16 Kbytes	1 Kbyte × 2	1 Kbyte	PLQP0032GB-A	K version	
R5F21276KXXXFP	32 Kbytes	1 Kbyte × 2	1.5 Kbytes	PLQP0032GB-A		

NOTE:

1. The user ROM is programmed before shipment.

2.1 Data Registers (R0, R1, R2, and R3)

R0 is a 16-bit register for transfer, arithmetic, and logic operations. The same applies to R1 to R3. R0 can be split into high-order bits (R0H) and low-order bits (R0L) to be used separately as 8-bit data registers. R1H and R1L are analogous to R0H and R0L. R2 can be combined with R0 and used as a 32-bit data register (R2R0). R3R1 is analogous to R2R0.

2.2 Address Registers (A0 and A1)

A0 is a 16-bit register for address register indirect addressing and address register relative addressing. It is also used for transfer, arithmetic, and logic operations. A1 is analogous to A0. A1 can be combined with A0 to be used as a 32-bit address register (A1A0).

2.3 Frame Base Register (FB)

FB is a 16-bit register for FB relative addressing.

2.4 Interrupt Table Register (INTB)

INTB is a 20-bit register that indicates the start address of an interrupt vector table.

2.5 Program Counter (PC)

PC is 20 bits wide and indicates the address of the next instruction to be executed.

2.6 User Stack Pointer (USP) and Interrupt Stack Pointer (ISP)

The stack pointers (SP), USP, and ISP, are each 16 bits wide. The U flag of FLG is used to switch between USP and ISP.

2.7 Static Base Register (SB)

SB is a 16-bit register for SB relative addressing.

2.8 Flag Register (FLG)

FLG is an 11-bit register indicating the CPU state.

2.8.1 Carry Flag (C)

The C flag retains carry, borrow, or shift-out bits that have been generated by the arithmetic and logic unit.

2.8.2 Debug Flag (D)

The D flag is for debugging only. Set it to 0.

2.8.3 Zero Flag (Z)

The Z flag is set to 1 when an arithmetic operation results in 0; otherwise to 0.

2.8.4 Sign Flag (S)

The S flag is set to 1 when an arithmetic operation results in a negative value; otherwise to 0.

2.8.5 Register Bank Select Flag (B)

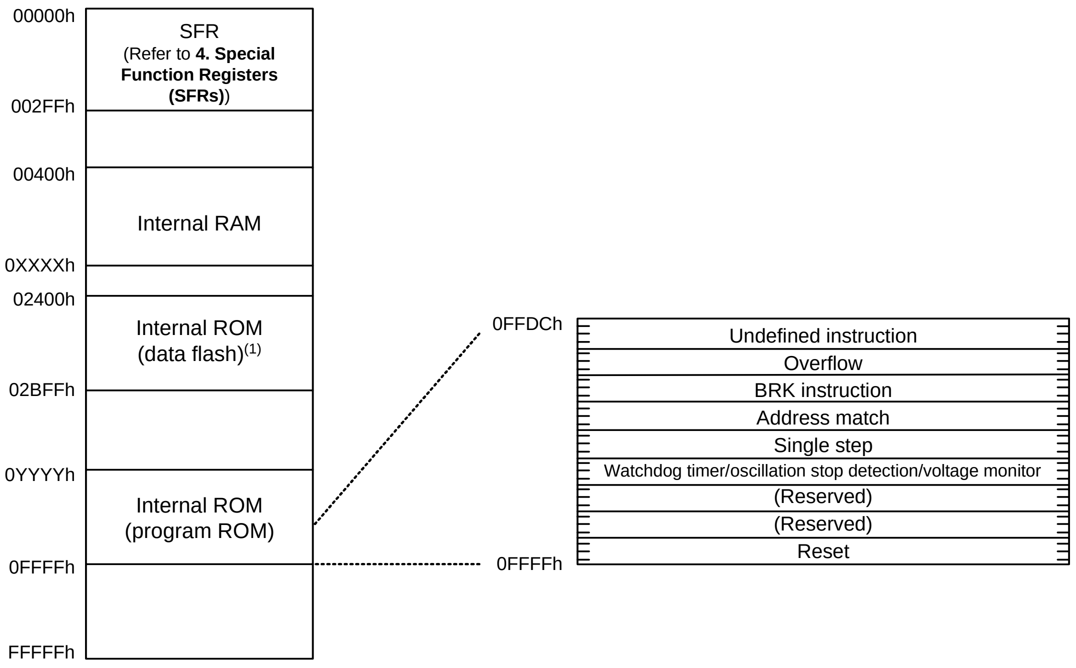
Register bank 0 is selected when the B flag is 0. Register bank 1 is selected when this flag is set to 1.

2.8.6 Overflow Flag (O)

The O flag is set to 1 when an operation results in an overflow; otherwise to 0.

3.2 R8C/27 Group

Figure 3.2 is a Memory Map of R8C/27 Group. The R8C/27 group has 1 Mbyte of address space from addresses 00000h to FFFFFh.
The internal ROM (program ROM) is allocated lower addresses, beginning with address 0FFFFh. For example, a 16-Kbyte internal ROM area is allocated addresses 0C000h to 0FFFFh.
The fixed interrupt vector table is allocated addresses 0FFDCh to 0FFFFh. They store the starting address of each interrupt routine.
The internal ROM (data flash) is allocated addresses 02400h to 02BFFh.
The internal RAM area is allocated higher addresses, beginning with address 00400h. For example, a 1-Kbyte internal RAM is allocated addresses 00400h to 007FFh. The internal RAM is used not only for storing data but also for calling subroutines and as stacks when interrupt requests are acknowledged.
Special function registers (SFRs) are allocated addresses 00000h to 002FFh. The peripheral function control registers are allocated here. All addresses within the SFR, which have nothing allocated are reserved for future use and cannot be accessed by users.



NOTES:
1. Data flash block A (1 Kbyte) and B (1 Kbyte) are shown.
2. The blank regions are reserved. Do not access locations in these regions.

Part Number	Internal ROM		Internal RAM	
	Size	Address 0YYYYh	Size	Address 0XXXXh
R5F21272SNFP, R5F21272SDFP, R5F21272SNXXXFP, R5F21272SDXXXFP	8 Kbytes	0E000h	512 bytes	005FFh
R5F21274SNFP, R5F21274SDFP, R5F21274JFP, R5F21274KFP, R5F21274SNXXXFP, R5F21274SDXXXFP, R5F21274JXXXFP, R5F21274KXXXFP	16 Kbytes	0C000h	1 Kbyte	007FFh
R5F21275SNFP, R5F21275SDFP, R5F21275SNXXXFP, R5F21275SDXXXFP	24 Kbytes	0A000h	1.5 Kbytes	009FFh
R5F21276SNFP, R5F21276SDFP, R5F21276JFP, R5F21276KFP, R5F21276SNXXXFP, R5F21276SDXXXFP, R5F21276JXXXFP, R5F21276KXXXFP	32 Kbytes	08000h	1.5 Kbytes	009FFh

Figure 3.2 Memory Map of R8C/27 Group

5. Electrical Characteristics

5.1 N, D Version

Table 5.1 Absolute Maximum Ratings

Symbol	Parameter	Condition	Rated Value	Unit
V_{CC}/AV_{CC}	Supply voltage		-0.3 to 6.5	V
V_I	Input voltage		-0.3 to V_{CC} + 0.3	V
V_O	Output voltage		-0.3 to V_{CC} + 0.3	V
P_d	Power dissipation	T_{opr} = 25°C	500	mW
T_{opr}	Operating ambient temperature		-20 to 85 (N version) / -40 to 85 (D version)	°C
T_{stg}	Storage temperature		-65 to 150	°C

Table 5.2 Recommended Operating Conditions

Symbol	Parameter		Conditions	Standard			Unit
				Min.	Typ.	Max.	
V_{CC}/AV_{CC}	Supply voltage			2.2	–	5.5	V
V_{SS}/AV_{SS}	Supply voltage			–	0	–	V
V_{IH}	Input “H” voltage			0.8 V_{CC}	–	V_{CC}	V
V_{IL}	Input “L” voltage			0	–	0.2 V_{CC}	V
$I_{OH(sum)}$	Peak sum output “H” current	Sum of all pins $I_{OH(peak)}$		–	–	-160	mA
$I_{OH(sum)}$	Average sum output “H” current	Sum of all pins $I_{OH(avg)}$		–	–	-80	mA
$I_{OH(peak)}$	Peak output “H” current	Except P1_0 to P1_7		–	–	-10	mA
		P1_0 to P1_7		–	–	-40	mA
$I_{OH(avg)}$	Average output “H” current	Except P1_0 to P1_7		–	–	-5	mA
		P1_0 to P1_7		–	–	-20	mA
$I_{OL(sum)}$	Peak sum output “L” currents	Sum of all pins $I_{OL(peak)}$		–	–	160	mA
$I_{OL(sum)}$	Average sum output “L” currents	Sum of all pins $I_{OL(avg)}$		–	–	80	mA
$I_{OL(peak)}$	Peak output “L” currents	Except P1_0 to P1_7		–	–	10	mA
		P1_0 to P1_7		–	–	40	mA
$I_{OL(avg)}$	Average output “L” current	Except P1_0 to P1_7		–	–	5	mA
		P1_0 to P1_7		–	–	20	mA
$f_{(XIN)}$	XIN clock input oscillation frequency		$3.0\ V \le V_{CC} \le 5.5\ V$	0	–	20	MHz
			$2.7\ V \le V_{CC} < 3.0\ V$	0	–	10	MHz
			$2.2\ V \le V_{CC} < 2.7\ V$	0	–	5	MHz
$f_{(XCIN)}$	XCIN clock input oscillation frequency		$2.2\ V \le V_{CC} \le 5.5\ V$	0	–	70	kHz
–	System clock	OCD2 = 0 XIN clock selected	$3.0\ V \le V_{CC} \le 5.5\ V$	0	–	20	MHz
			$2.7\ V \le V_{CC} < 3.0\ V$	0	–	10	MHz
			$2.2\ V \le V_{CC} < 2.7\ V$	0	–	5	MHz
		OCD2 = 1 On-chip oscillator clock selected	FRA01 = 0 Low-speed on-chip oscillator clock selected	–	125	–	kHz
			FRA01 = 1 High-speed on-chip oscillator clock selected $3.0\ V \le V_{CC} \le 5.5\ V$	–	–	20	MHz
			FRA01 = 1 High-speed on-chip oscillator clock selected $2.7\ V \le V_{CC} \le 5.5\ V$	–	–	10	MHz
			FRA01 = 1 High-speed on-chip oscillator clock selected $2.2\ V \le V_{CC} \le 5.5\ V$	–	–	5	MHz

NOTES:

1. V_{CC} = 2.2 to 5.5 V at T_{opr} = -20 to 85°C (N version) / -40 to 85°C (D version), unless otherwise specified.
2. The average output current indicates the average value of current measured during 100 ms.

Table 5.4 Flash Memory (Program ROM) Electrical Characteristics

Symbol	Parameter	Conditions	Standard			Unit
			Min.	Typ.	Max.	
–	Program/erase endurance[2]	R8C/26 Group	100[3]	–	–	times
		R8C/27 Group	1,000[3]	–	–	times
–	Byte program time		–	50	400	µs
–	Block erase time		–	0.4	9	s
$t_{d(SR-SUS)}$	Time delay from suspend request until suspend		–	–	97 + CPU clock × 6 cycles	µs
–	Interval from erase start/restart until following suspend request		650	–	–	µs
–	Interval from program start/restart until following suspend request		0	–	–	ns
–	Time from suspend until program/erase restart		–	–	3 + CPU clock × 4 cycles	µs
–	Program, erase voltage		2.7	–	5.5	V
–	Read voltage		2.2	–	5.5	V
–	Program, erase temperature		0	–	60	°C
–	Data hold time[7]	Ambient temperature = 55°C	20	–	–	year

NOTES:

1. V_{CC} = 2.7 to 5.5 V at T_{opr} = 0 to 60°C, unless otherwise specified.
2. Definition of programming/erasure endurance
   The programming and erasure endurance is defined on a per-block basis.
   If the programming and erasure endurance is n (n = 100 or 1,000), each block can be erased n times. For example, if 1,024 1-byte writes are performed to different addresses in block A, a 1 Kbyte block, and then the block is erased, the programming/erasure endurance still stands at one.
   However, the same address must not be programmed more than once per erase operation (overwriting prohibited).
3. Endurance to guarantee all electrical characteristics after program and erase. (1 to Min. value can be guaranteed).
4. In a system that executes multiple programming operations, the actual erasure count can be reduced by writing to sequential addresses in turn so that as much of the block as possible is used up before performing an erase operation. For example, when programming groups of 16 bytes, the effective number of rewrites can be minimized by programming up to 128 groups before erasing them all in one operation. It is also advisable to retain data on the erasure endurance of each block and limit the number of erase operations to a certain number.
5. If an error occurs during block erase, attempt to execute the clear status register command, then execute the block erase command at least three times until the erase error does not occur.
6. Customers desiring program/erase failure rate information should contact their Renesas technical support representative.
7. The data hold time includes time that the power supply is off or the clock is not supplied.

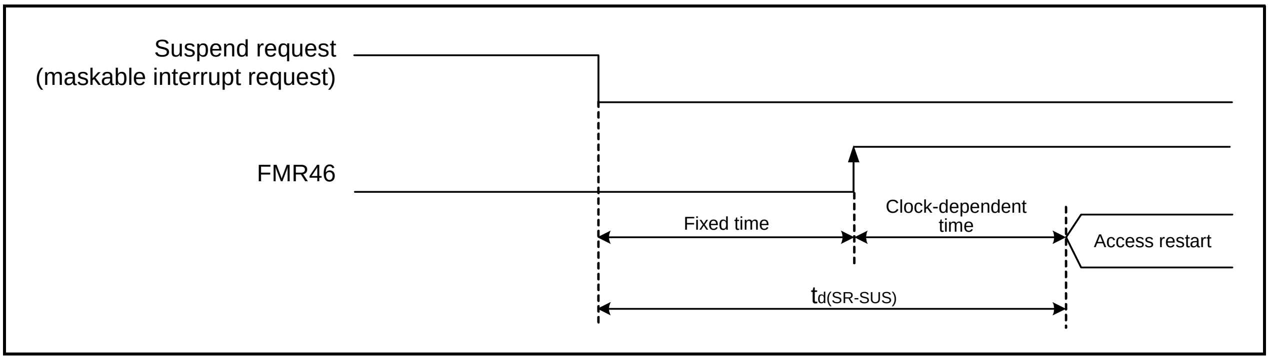


Figure 5.2 Time delay until Suspend

Table 5.6 Voltage Detection 0 Circuit Electrical Characteristics

Symbol	Parameter	Condition	Standard			Unit
			Min.	Typ.	Max.	
V_{det0}	Voltage detection level		2.2	2.3	2.4	V
–	Voltage detection circuit self power consumption	VCA25 = 1, V_{CC} = 5.0 V	–	0.9	–	µA
$t_{d(E-A)}$	Waiting time until voltage detection circuit operation starts(2)		–	–	300	µs
Vccmin	MCU operating voltage minimum value		2.2	–	–	V

NOTES:
1. The measurement condition is V_{CC} = 2.2 to 5.5 V and T_{opr} = -20 to 85°C (N version) / -40 to 85°C (D version).
2. Necessary time until the voltage detection circuit operates when setting to 1 again after setting the VCA25 bit in the VCA2 register to 0.

Table 5.7 Voltage Detection 1 Circuit Electrical Characteristics

Symbol	Parameter	Condition	Standard			Unit
			Min.	Typ.	Max.	
V_{det1}	Voltage detection level(4)		2.70	2.85	3.00	V
–	Voltage monitor 1 interrupt request generation time(2)		–	40	–	µs
–	Voltage detection circuit self power consumption	VCA26 = 1, V_{CC} = 5.0 V	–	0.6	–	µA
$t_{d(E-A)}$	Waiting time until voltage detection circuit operation starts(3)		–	–	100	µs

NOTES:
1. The measurement condition is V_{CC} = 2.2 to 5.5 V and T_{opr} = -20 to 85°C (N version) / -40 to 85°C (D version).
2. Time until the voltage monitor 1 interrupt request is generated after the voltage passes V_{det1}.
3. Necessary time until the voltage detection circuit operates when setting to 1 again after setting the VCA26 bit in the VCA2 register to 0.
4. This parameter shows the voltage detection level when the power supply drops.
   The voltage detection level when the power supply rises is higher than the voltage detection level when the power supply drops by approximately 0.1 V.

Table 5.8 Voltage Detection 2 Circuit Electrical Characteristics

Symbol	Parameter	Condition	Standard			Unit
			Min.	Typ.	Max.	
V_{det2}	Voltage detection level		3.3	3.6	3.9	V
–	Voltage monitor 2 interrupt request generation time(2)		–	40	–	µs
–	Voltage detection circuit self power consumption	VCA27 = 1, V_{CC} = 5.0 V	–	0.6	–	µA
$t_{d(E-A)}$	Waiting time until voltage detection circuit operation starts(3)		–	–	100	µs

NOTES:
1. The measurement condition is V_{CC} = 2.2 to 5.5 V and T_{opr} = -20 to 85°C (N version) / -40 to 85°C (D version).
2. Time until the voltage monitor 2 interrupt request is generated after the voltage passes V_{det2}.
3. Necessary time until the voltage detection circuit operates after setting to 1 again after setting the VCA27 bit in the VCA2 register to 0.

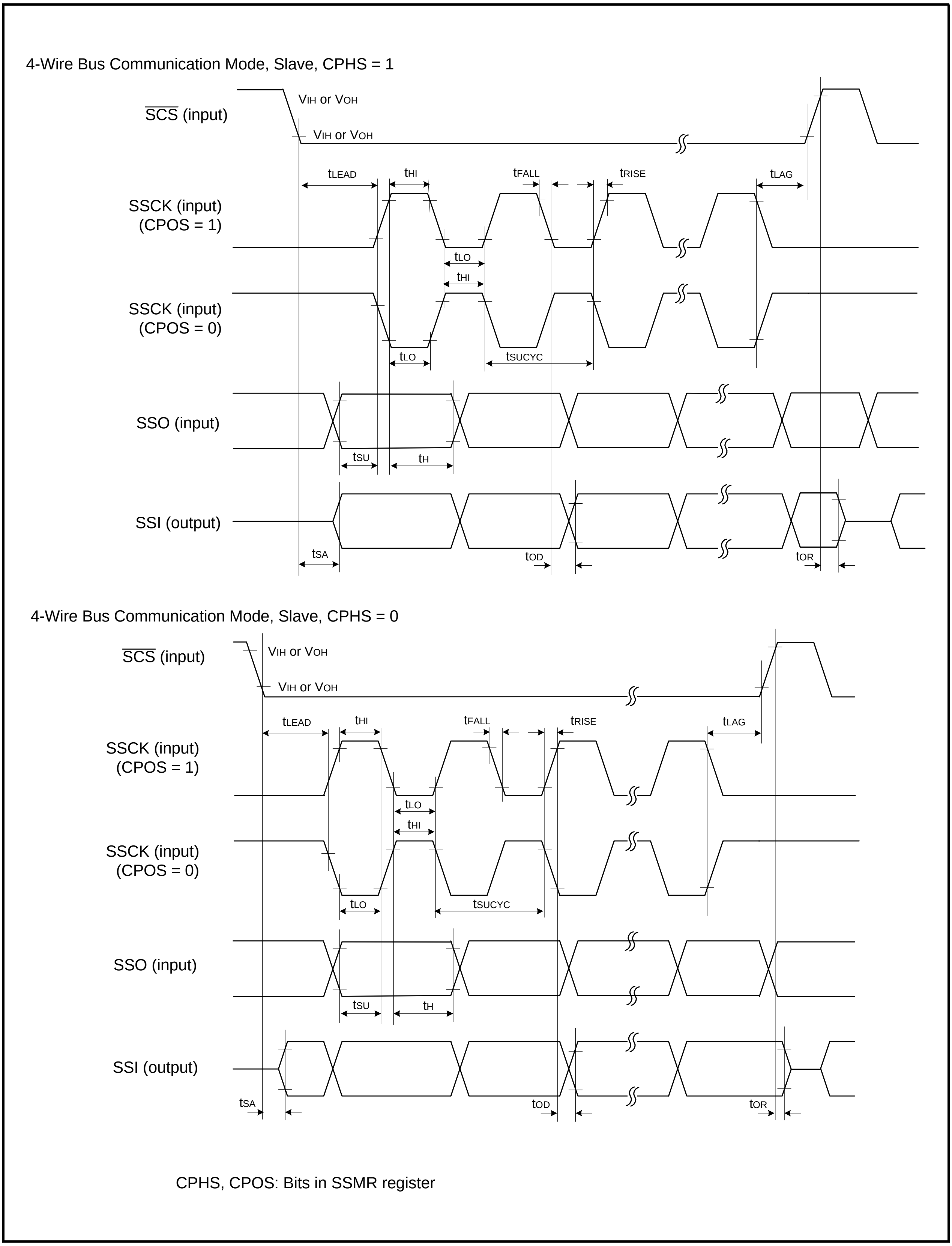


Figure 5.5 I/O Timing of Clock Synchronous Serial I/O with Chip Select (Slave)

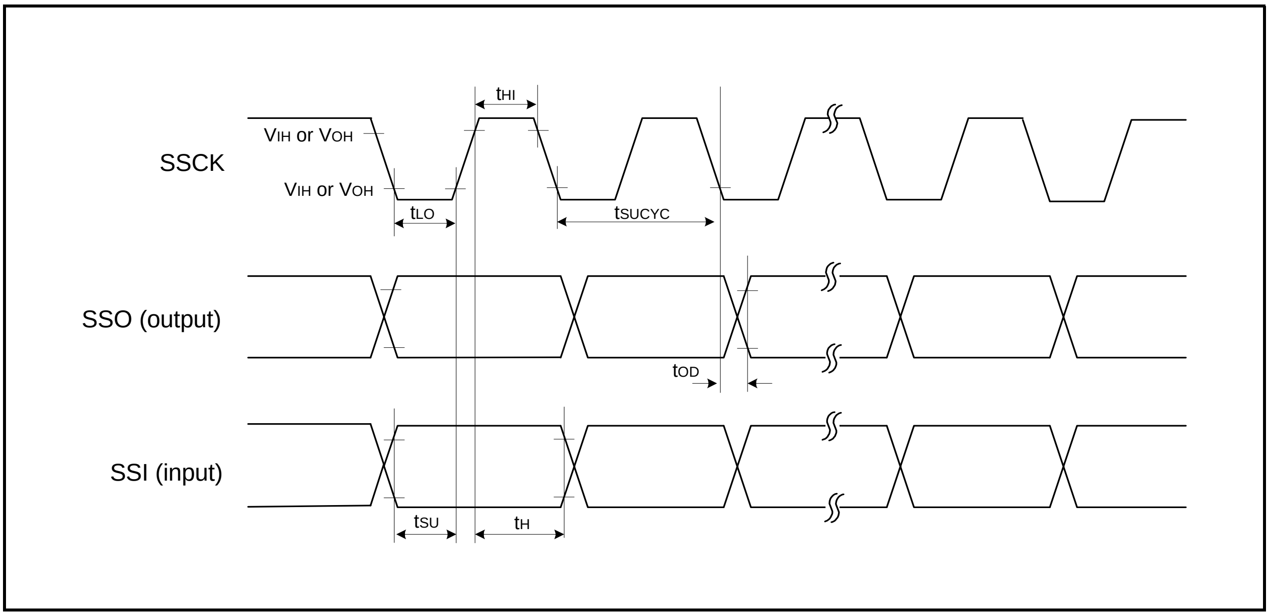


Figure 5.6 I/O Timing of Clock Synchronous Serial I/O with Chip Select (Clock Synchronous Communication Mode)

Table 5.20 Serial Interface

Symbol	Parameter	Standard		Unit
		Min.	Max.	
$t_{c(CK)}$	CLKi input cycle time	200	–	ns
$t_{W(CKH)}$	CLKi input “H” width	100	–	ns
$t_{W(CKL)}$	CLKi input “L” width	100	–	ns
$t_{d(C-Q)}$	TXDi output delay time	–	50	ns
$t_{h(C-Q)}$	TXDi hold time	0	–	ns
$t_{su(D-C)}$	RXDi input setup time	50	–	ns
$t_{h(C-D)}$	RXDi input hold time	90	–	ns

i = 0 or 1

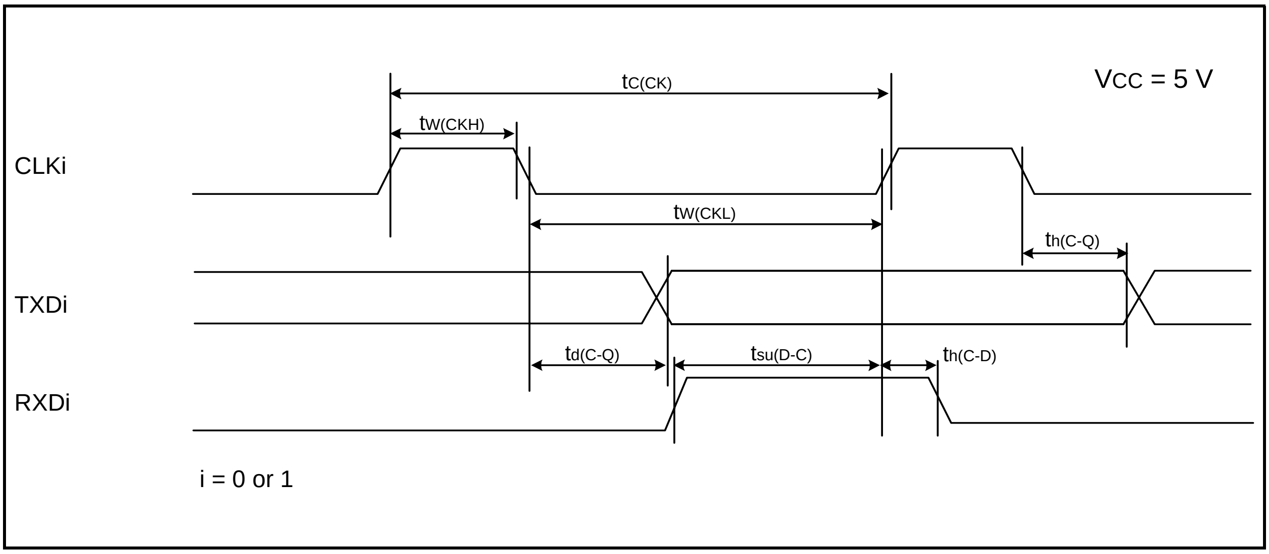


Figure 5.10 Serial Interface Timing Diagram when V_{CC} = 5 V

Table 5.21 External Interrupt $\overline{\text{INTi}}$ (i = 0, 1, 3) Input

Symbol	Parameter	Standard		Unit
		Min.	Max.	
$t_{W(INH)}$	$\overline{\text{INTi}}$ input “H” width	250(1)	–	ns
$t_{W(INL)}$	$\overline{\text{INTi}}$ input “L” width	250(2)	–	ns

NOTES:

1. When selecting the digital filter by the $\overline{\text{INTi}}$ input filter select bit, use an $\overline{\text{INTi}}$ input HIGH width of either (1/digital filter clock frequency × 3) or the minimum value of standard, whichever is greater.
2. When selecting the digital filter by the $\overline{\text{INTi}}$ input filter select bit, use an $\overline{\text{INTi}}$ input LOW width of either (1/digital filter clock frequency × 3) or the minimum value of standard, whichever is greater.

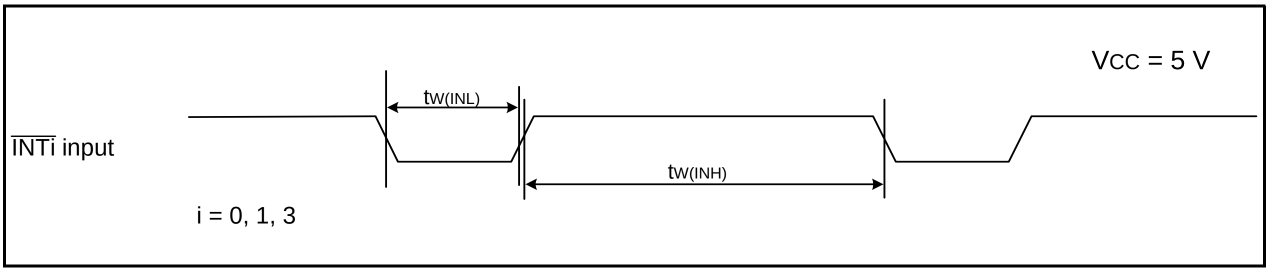


Figure 5.11 External Interrupt $\overline{\text{INTi}}$ Input Timing Diagram when V_{CC} = 5 V

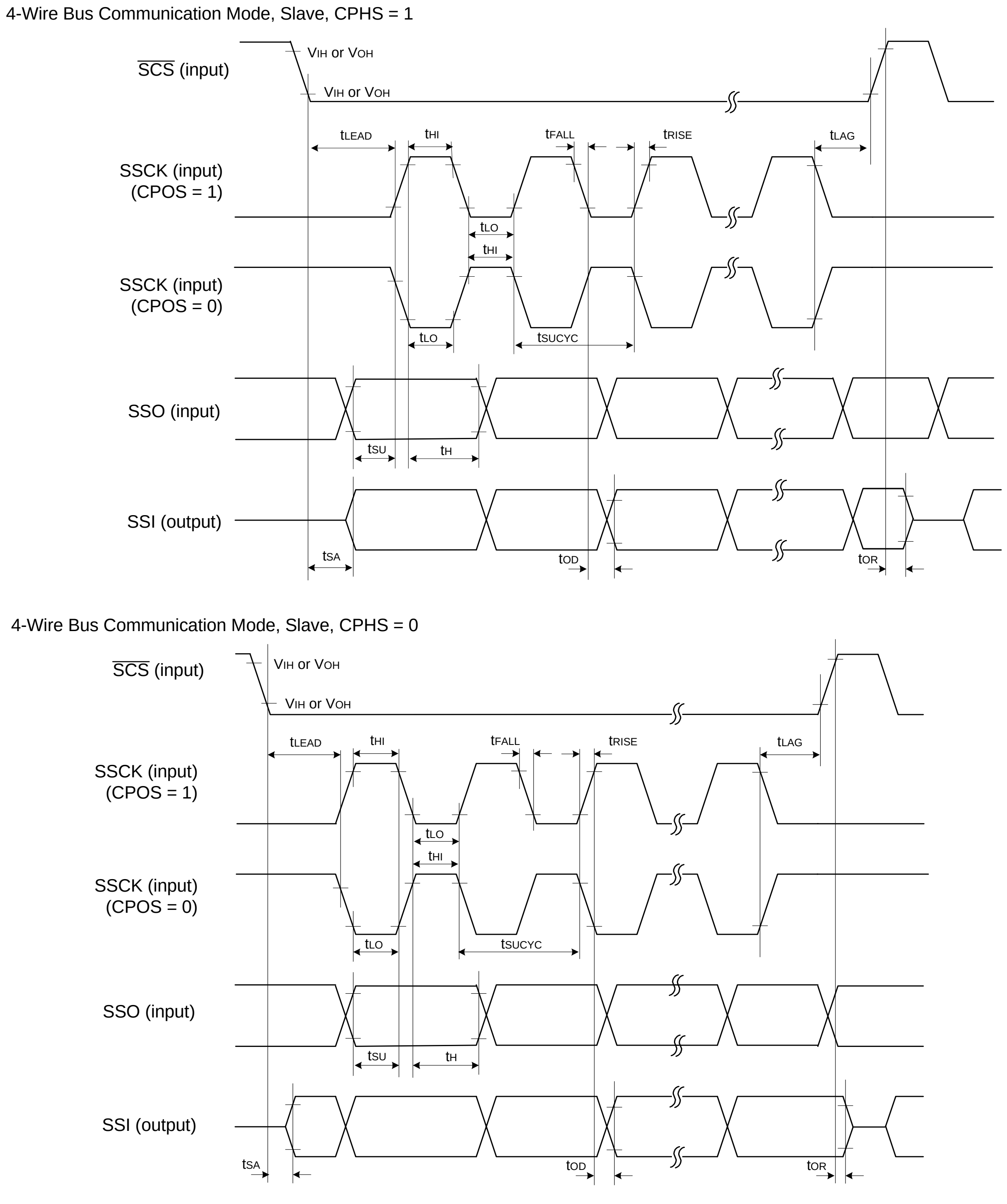
Table 5.29 Electrical Characteristics (6) [Vcc = 2.2 V] (Topr = -20 to 85°C (N version) / -40 to 85°C (D version), unless otherwise specified.)

Symbol	Parameter	Condition		Standard			Unit
				Min.	Typ.	Max.	
ICC	Power supply current (VCC = 2.2 to 2.7 V) Single-chip mode, output pins are open, other pins are VSS	High-speed clock mode	XIN = 5 MHz (square wave) High-speed on-chip oscillator off Low-speed on-chip oscillator on = 125 kHz No division	–	3.5	–	mA
			XIN = 5 MHz (square wave) High-speed on-chip oscillator off Low-speed on-chip oscillator on = 125 kHz Divide-by-8	–	1.5	–	mA
		High-speed on-chip oscillator mode	XIN clock off High-speed on-chip oscillator on fOCO = 5 MHz Low-speed on-chip oscillator on = 125 kHz No division	–	3.5	–	mA
			XIN clock off High-speed on-chip oscillator on fOCO = 5 MHz Low-speed on-chip oscillator on = 125 kHz Divide-by-8	–	1.5	–	mA
		Low-speed on-chip oscillator mode	XIN clock off High-speed on-chip oscillator off Low-speed on-chip oscillator on = 125 kHz Divide-by-8, FMR47 = 1	–	100	230	µA
		Low-speed clock mode	XIN clock off High-speed on-chip oscillator off Low-speed on-chip oscillator off XCIN clock oscillator on = 32 kHz FMR47 = 1	–	100	230	µA
			XIN clock off High-speed on-chip oscillator off Low-speed on-chip oscillator off XCIN clock oscillator on = 32 kHz Program operation on RAM Flash memory off, FMSTP = 1	–	25	–	µA
		Wait mode	XIN clock off High-speed on-chip oscillator off Low-speed on-chip oscillator on = 125 kHz While a WAIT instruction is executed Peripheral clock operation VCA27 = VCA26 = VCA25 = 0 VCA20 = 1	–	22	60	µA
			XIN clock off High-speed on-chip oscillator off Low-speed on-chip oscillator on = 125 kHz While a WAIT instruction is executed Peripheral clock off VCA27 = VCA26 = VCA25 = 0 VCA20 = 1	–	20	55	µA
			XIN clock off High-speed on-chip oscillator off Low-speed on-chip oscillator off XCIN clock oscillator on = 32 kHz (high drive) While a WAIT instruction is executed VCA27 = VCA26 = VCA25 = 0 VCA20 = 1	–	3.0	–	µA
			XIN clock off High-speed on-chip oscillator off Low-speed on-chip oscillator off XCIN clock oscillator on = 32 kHz (low drive) While a WAIT instruction is executed VCA27 = VCA26 = VCA25 = 0 VCA20 = 1	–	1.8	–	µA
		Stop mode	XIN clock off, Topr = 25°C High-speed on-chip oscillator off Low-speed on-chip oscillator off CM10 = 1 Peripheral clock off VCA27 = VCA26 = VCA25 = 0	–	0.7	3.0	µA
			XIN clock off, Topr = 85°C High-speed on-chip oscillator off Low-speed on-chip oscillator off CM10 = 1 Peripheral clock off VCA27 = VCA26 = VCA25 = 0	–	1.1	–	µA

Table 5.45 Timing Requirements of Clock Synchronous Serial I/O with Chip Select(1)

Symbol	Parameter		Conditions	Standard			Unit
				Min.	Typ.	Max.	
t_{SUCYC}	SSCK clock cycle time			4	–	–	t_{CYC}(2)
t_{HI}	SSCK clock “H” width			0.4	–	0.6	t_{SUCYC}
t_{LO}	SSCK clock “L” width			0.4	–	0.6	t_{SUCYC}
t_{RISE}	SSCK clock rising time	Master		–	–	1	t_{CYC}(2)
		Slave		–	–	1	µs
t_{FALL}	SSCK clock falling time	Master		–	–	1	t_{CYC}(2)
		Slave		–	–	1	µs
t_{SU}	SSO, SSI data input setup time			100	–	–	ns
t_H	SSO, SSI data input hold time			1	–	–	t_{CYC}(2)
t_{LEAD}	$\overline{SCS}$ setup time	Slave		1t_{CYC} + 50	–	–	ns
t_{LAG}	$\overline{SCS}$ hold time	Slave		1t_{CYC} + 50	–	–	ns
t_{OD}	SSO, SSI data output delay time			–	–	1	t_{CYC}(2)
t_{SA}	SSI slave access time			–	–	1.5t_{CYC} + 100	ns
t_{OR}	SSI slave out open time			–	–	1.5t_{CYC} + 100	ns

NOTES:
1. V_{CC} = 2.7 to 5.5 V, V_{SS} = 0 V at T_{opr} = -40 to 85°C (J version) / -40 to 125°C (K version), unless otherwise specified.
2. 1t_{CYC} = 1/f1(s)



4-Wire Bus Communication Mode, Slave, CPHS = 1

4-Wire Bus Communication Mode, Slave, CPHS = 0

CPHS, CPOS: Bits in SSMR register

Figure 5.24 I/O Timing of Clock Synchronous Serial I/O with Chip Select (Slave)

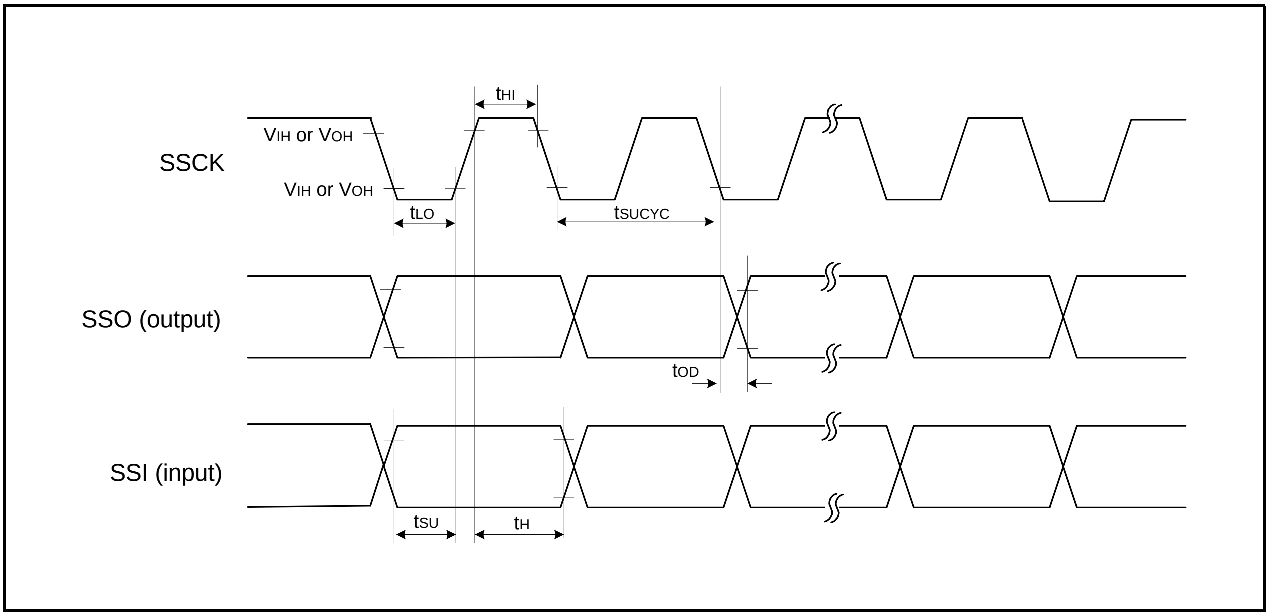


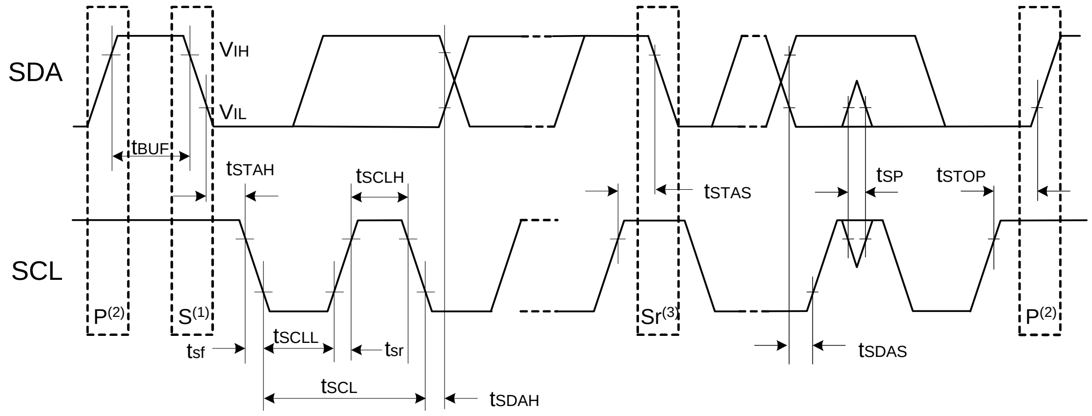
Figure 5.25 I/O Timing of Clock Synchronous Serial I/O with Chip Select (Clock Synchronous Communication Mode)

Table 5.46 Timing Requirements of I^{2}C bus Interface(1)

Symbol	Parameter	Condition	Standard			Unit
			Min.	Typ.	Max.	
t_{SCL}	SCL input cycle time		$12t_{CYC} + 600$(2)	–	–	ns
t_{SCLH}	SCL input “H” width		$3t_{CYC} + 300$(2)	–	–	ns
t_{SCLL}	SCL input “L” width		$5t_{CYC} + 500$(2)	–	–	ns
t_{sf}	SCL, SDA input fall time		–	–	300	ns
t_{SP}	SCL, SDA input spike pulse rejection time		–	–	$1t_{CYC}$(2)	ns
t_{BUF}	SDA input bus-free time		$5t_{CYC}$(2)	–	–	ns
t_{STAH}	Start condition input hold time		$3t_{CYC}$(2)	–	–	ns
t_{STAS}	Retransmit start condition input setup time		$3t_{CYC}$(2)	–	–	ns
t_{STOP}	Stop condition input setup time		$3t_{CYC}$(2)	–	–	ns
t_{SDAS}	Data input setup time		$1t_{CYC} + 20$(2)	–	–	ns
t_{SDAH}	Data input hold time		0	–	–	ns

NOTES:

1. V_{CC} = 2.7 to 5.5 V, V_{SS} = 0 V at T_{opr} = -40 to 85°C (J version) / -40 to 125°C (K version), unless otherwise specified.
2. $1t_{CYC} = 1/f1(s)$



NOTES:
1. Start condition
2. Stop condition
3. Retransmit start condition

Figure 5.26 I/O Timing of I^{2}C bus Interface

Table 5.47 Electrical Characteristics (1) [V_{CC} = 5 V]

Symbol	Parameter		Condition		Standard			Unit
					Min.	Typ.	Max.	
V_{OH}	Output "H" voltage	Except XOUT	I_{OH} = -5 mA		V_{CC} - 2.0	–	V_{CC}	V
			I_{OH} = -200 μA		V_{CC} - 0.3	–	V_{CC}	V
		XOUT	Drive capacity HIGH	I_{OH} = -1 mA	V_{CC} - 2.0	–	V_{CC}	V
			Drive capacity LOW	I_{OH} = -500 μA	V_{CC} - 2.0	–	V_{CC}	V
V_{OL}	Output "L" voltage	Except XOUT	I_{OL} = 5 mA		–	–	2.0	V
			I_{OL} = 200 μA		–	–	0.45	V
		XOUT	Drive capacity HIGH	I_{OL} = 1 mA	–	–	2.0	V
			Drive capacity LOW	I_{OL} = 500 μA	–	–	2.0	V
V_{T+}-V_{T-}	Hysteresis	$\overline{\text{INT0}}$, $\overline{\text{INT1}}$, $\overline{\text{INT3}}$, $\overline{\text{KI0}}$, $\overline{\text{KI1}}$, $\overline{\text{KI2}}$, $\overline{\text{KI3}}$, TRAIO, RXD0, RXD1, CLK0, CLK1, SSI, SCL, SDA, SSO			0.1	0.5	–	V
		$\overline{\text{RESET}}$			0.1	1.0	–	V
I_{IH}	Input "H" current		VI = 5 V, V_{CC} = 5V		–	–	5.0	μA
I_{IL}	Input "L" current		VI = 0 V, V_{CC} = 5V		–	–	-5.0	μA
R_{PULLUP}	Pull-up resistance		VI = 0 V, V_{CC} = 5V		30	50	167	kΩ
R_{fXIN}	Feedback resistance	XIN			–	1.0	–	MΩ
V_{RAM}	RAM hold voltage		During stop mode		2.0	–	–	V

NOTE:

1. V_{CC} = 4.2 to 5.5 V at T_{opr} = -40 to 85°C (J version) / -40 to 125°C (K version), f(XIN) = 20 MHz, unless otherwise specified.

Table 5.53 Electrical Characteristics (3) [V_{CC} = 3 V]

Symbol	Parameter		Condition		Standard			Unit
					Min.	Typ.	Max.	
V_{OH}	Output “H” voltage	Except XOUT	I_{OH} = -1 mA		V_{CC} - 0.5	–	V_{CC}	V
		XOUT	Drive capacity HIGH	I_{OH} = -0.1 mA	V_{CC} - 0.5	–	V_{CC}	V
			Drive capacity LOW	I_{OH} = -50 µA	V_{CC} - 0.5	–	V_{CC}	V
V_{OL}	Output “L” voltage	Except XOUT	I_{OL} = 1 mA		–	–	0.5	V
		XOUT	Drive capacity HIGH	I_{OL} = 0.1 mA	–	–	0.5	V
			Drive capacity LOW	I_{OL} = 50 µA	–	–	0.5	V
V_{T+}-V_{T-}	Hysteresis	$\overline{\text{INT0}}$, $\overline{\text{INT1}}$, $\overline{\text{INT3}}$, $\overline{\text{KI0}}$, $\overline{\text{KI1}}$, $\overline{\text{KI2}}$, $\overline{\text{KI3}}$, TRAIO, RXD0, RXD1, CLK0,CLK1, SSI, SCL, SDA, SSO			0.1	0.3	–	V
		$\overline{\text{RESET}}$			0.1	0.4	–	V
I_{IH}	Input “H” current		VI = 3 V, V_{CC} = 3V		–	–	4.0	µA
I_{IL}	Input “L” current		VI = 0 V, V_{CC} = 3V		–	–	-4.0	µA
R_{PULLUP}	Pull-up resistance		VI = 0 V, V_{CC} = 3V		66	160	500	kΩ
R_{fXIN}	Feedback resistance	XIN			–	3.0	–	MΩ
V_{RAM}	RAM hold voltage		During stop mode		2.0	–	–	V

NOTE:

1. V_{CC} = 2.7 to 3.3 V at T_{opr} = -40 to 85°C (J version) / -40 to 125°C (K version), f(XIN) = 10 MHz, unless otherwise specified.

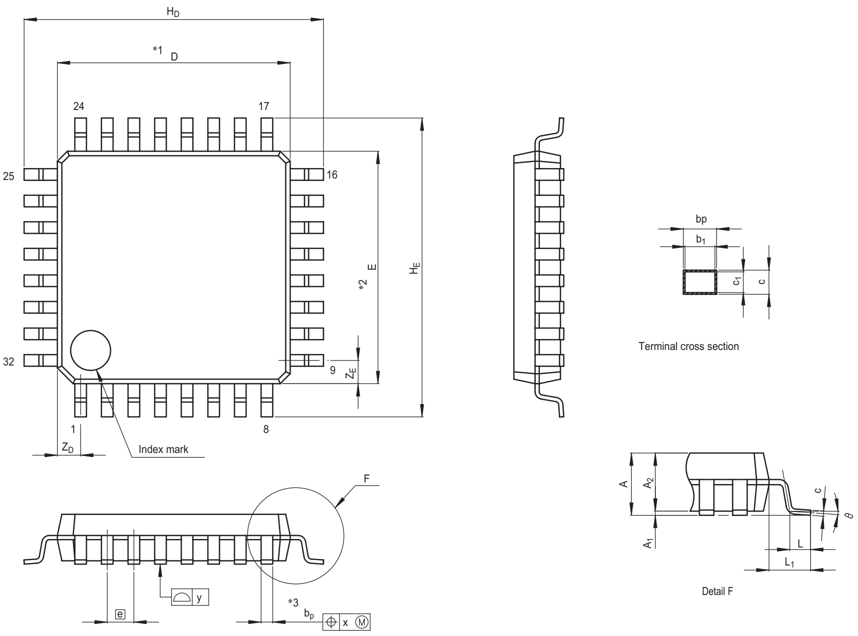
Table 5.54 Electrical Characteristics (4) [Vcc = 3 V]
(T_{opr} = -40 to 85°C (J version) / -40 to 125°C (K version), unless otherwise specified.)

Symbol	Parameter	Condition		Standard			Unit
				Min.	Typ.	Max.	
I_{CC}	Power supply current (V_{CC} = 2.7 to 3.3 V) Single-chip mode, output pins are open, other pins are V_{SS}	High-speed clock mode	XIN = 10 MHz (square wave) High-speed on-chip oscillator off Low-speed on-chip oscillator on = 125 kHz No division	–	6	–	mA
			XIN = 10 MHz (square wave) High-speed on-chip oscillator off Low-speed on-chip oscillator on = 125 kHz Divide-by-8	–	2	–	mA
		High-speed on-chip oscillator mode	XIN clock off High-speed on-chip oscillator on fOCO = 10 MHz Low-speed on-chip oscillator on = 125 kHz No division	–	5	9	mA
			XIN clock off High-speed on-chip oscillator on fOCO = 10 MHz Low-speed on-chip oscillator on = 125 kHz Divide-by-8	–	2	–	mA
		Low-speed on-chip oscillator mode	XIN clock off High-speed on-chip oscillator off Low-speed on-chip oscillator on = 125 kHz Divide-by-8, FMR47 = 1	–	130	300	µA
		Wait mode	XIN clock off High-speed on-chip oscillator off Low-speed on-chip oscillator on = 125 kHz While a WAIT instruction is executed Peripheral clock operation VCA27 = VCA26 = VCA25 = 0 VCA20 = 1	–	25	70	µA
			XIN clock off High-speed on-chip oscillator off Low-speed on-chip oscillator on = 125 kHz While a WAIT instruction is executed Peripheral clock off VCA27 = VCA26 = VCA25 = 0 VCA20 = 1	–	23	55	µA
		Stop mode	XIN clock off, T_{opr} = 25°C High-speed on-chip oscillator off Low-speed on-chip oscillator off CM10 = 1 Peripheral clock off VCA27 = VCA26 = VCA25 = 0	–	0.7	3.0	µA
			XIN clock off, T_{opr} = 85°C High-speed on-chip oscillator off Low-speed on-chip oscillator off CM10 = 1 Peripheral clock off VCA27 = VCA26 = VCA25 = 0	–	1.1	–	µA
			XIN clock off, T_{opr} = 125°C High-speed on-chip oscillator off Low-speed on-chip oscillator off CM10 = 1 Peripheral clock off VCA27 = VCA26 = VCA25 = 0	–	3.8	–	µA

Package Dimensions

Diagrams showing the latest package dimensions and mounting information are available in the “Packages” section of the Renesas Technology website.

JEITA Package Code	RENESAS Code	Previous Code	MASS[Typ.]
P-LQFP32-7x7-0.80	PLQP0032GB-A	32P6U-A	0.2g



NOTE)
1. DIMENSIONS "*1" AND "*2" DO NOT INCLUDE MOLD FLASH.
2. DIMENSION "*3" DOES NOT INCLUDE TRIM OFFSET.

Reference Symbol	Dimension in Millimeters		
	Min	Nom	Max
D	6.9	7.0	7.1
E	6.9	7.0	7.1
A_2	—	1.4	—
H_D	8.8	9.0	9.2
H_E	8.8	9.0	9.2
A	—	—	1.7
A_1	0	0.1	0.2
b_p	0.32	0.37	0.42
b_1	—	0.35	—
c	0.09	0.145	0.20
c_1	—	0.125	—
θ	0°	—	8°
$\boxed{e}$	—	0.8	—
x	—	—	0.20
y	—	—	0.10
Z_D	—	0.7	—
Z_E	—	0.7	—
L	0.3	0.5	0.7
L_1	—	1.0	—